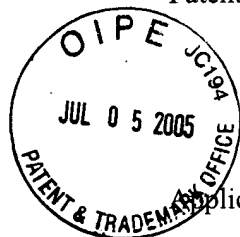


DTW

Patent Application 10/731,346

Docket No. TS02-1367 (24061.504)  
Customer No. 42717



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Fang-Cheng Chen, et al.	§	Docket No.:	TS02-1367
		§		(24061.504)
Serial No.:	10/731,346	§		
		§	Examiner:	Thanh T. Nguyen
Filed:	December 9, 2003	§		
		§	Art Unit:	2813
For:	Method of Forming a	§		
	Semiconductor Device with a High	§	Conf. No.:	3543
	Dielectric Constant Material and	§		
	an Offset Spacer	§		

**RESPONSE TO RESTRICTION REQUIREMENT**

Commissioner for Patents  
Mail Stop: Amendment  
PO Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

The present paper is being submitted in response to the Restriction Requirement Office Action dated June 1, 2005 in the above-identified application.

**Election of Claims** begins on page 2 of this paper.

**Amendments to the Claims** are reflected in the Listing of Claims which begins on page 3 of this paper.

**Remarks** begin on page 7 of this paper.

**I. Election**

In the Office Action mailed June 1, 2005, the Examiner alleges that the application contains claims directed to two inventions and, thus, required restriction of either:

Claims 1-18 (Group I), drawn to a method of forming a semiconductor device on a semiconductor substrate; or

Claims 19-28 (Group II), drawn to a MOSFET device structure.

In response, Applicants hereby elect Group I, corresponding to claims 1-18. Applicants' election is made with traverse on the grounds that the embodiments delineated by the Examiner are not patentably distinct and therefore constitute a single invention concept.